

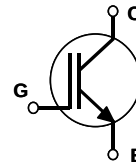
TO-3P


Features

- High speed switching
- Low saturation voltage : $V_{CE(sat)} = 2.5\text{ V @ } I_C = 25\text{ A}$
- High input impedance

General Description

Employing NPT technology, Kersemi AN series of provides low conduction and switching losses. The AN series offers an solution for application such as induction heating (IH), motor control, general purpose inverters and uninterruptible power supplies (UPS).



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	FGA25N120AN	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	40	A
	Collector Current @ $T_C = 100^\circ\text{C}$	25	A
$I_{CM(1)}$	Pulsed Collector Current	75	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	310	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	125	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 3mA	1200	--	--	V
ΔBV _{CES} /ΔT _J	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 3mA	--	0.6	--	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	--	--	3	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	--	--	± 100	nA

On Characteristics

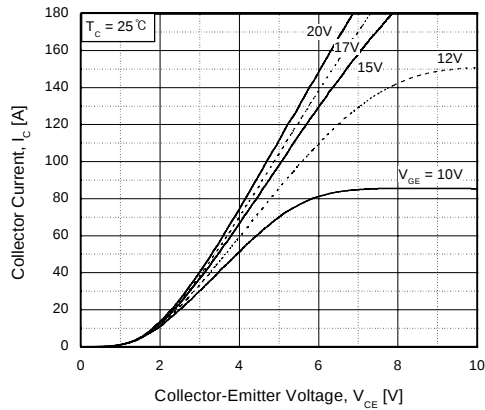
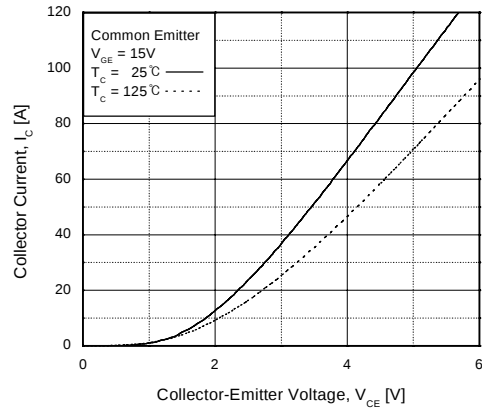
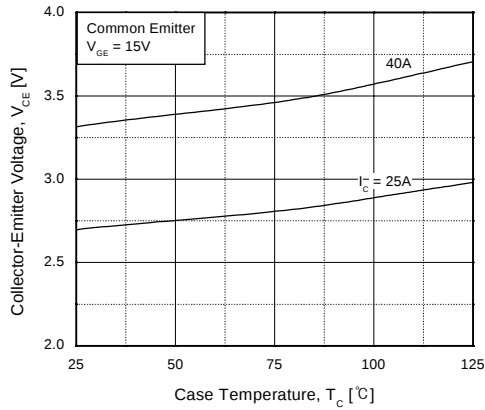
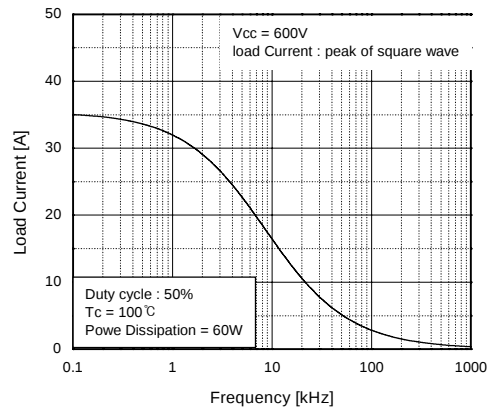
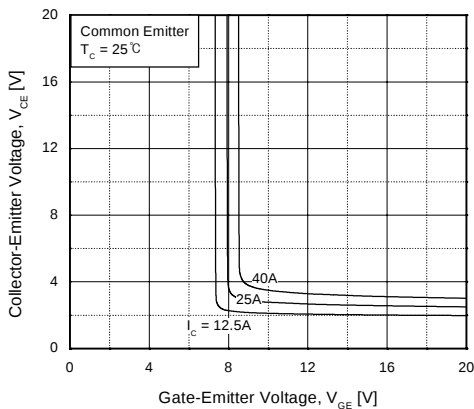
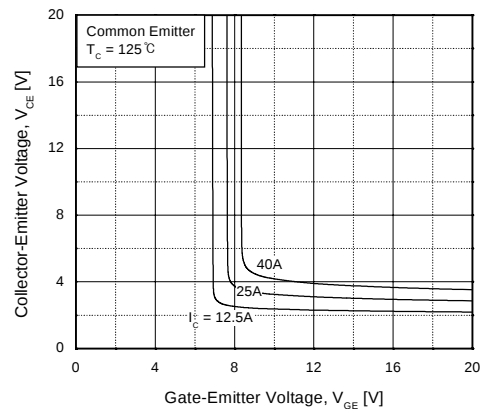
V _{GE(th)}	G-E Threshold Voltage	I _C = 25mA, V _{CE} = V _{GE}	3.5	5.5	7.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 25A, V _{GE} = 15V	--	2.5	3.2	V
		I _C = 25A, V _{GE} = 15V, T _C = 125°C	--	2.9	--	V
		I _C = 40A, V _{GE} = 15V	--	3.1	--	V

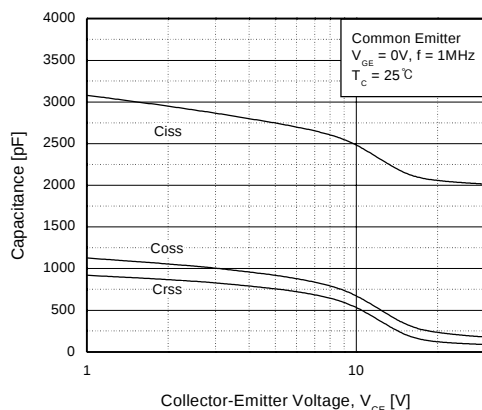
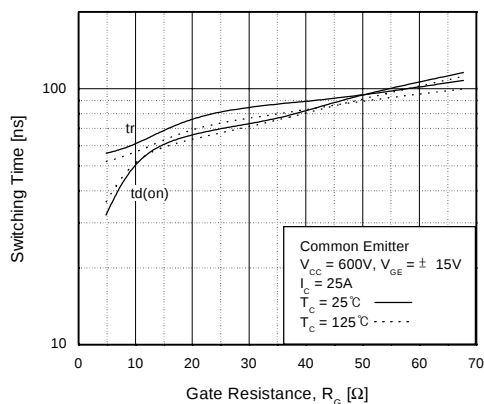
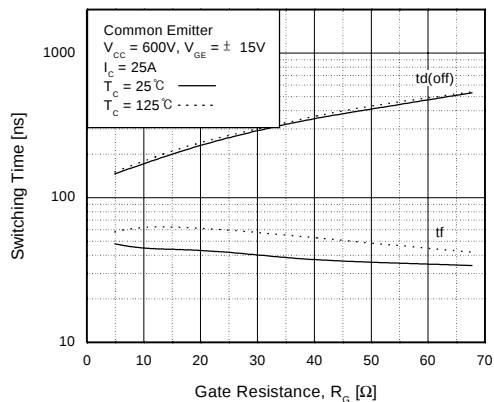
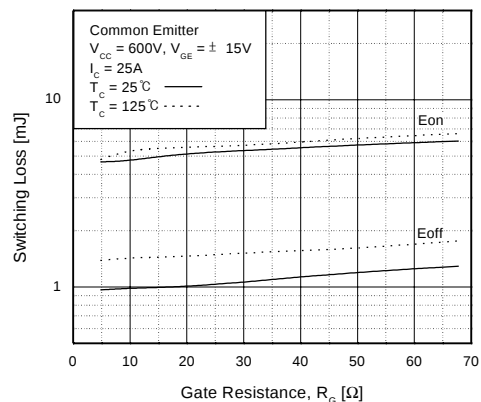
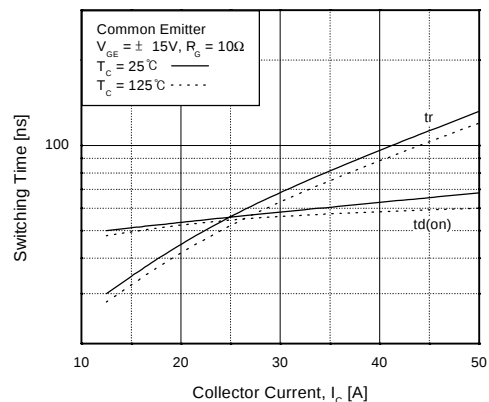
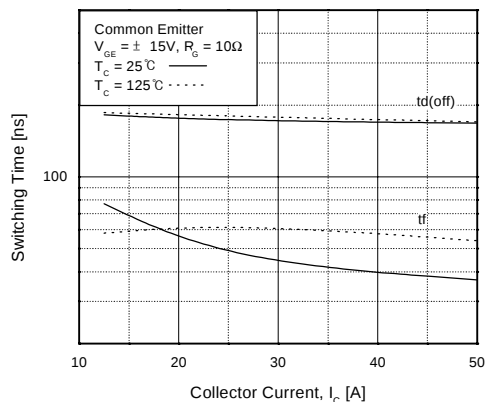
Dynamic Characteristics

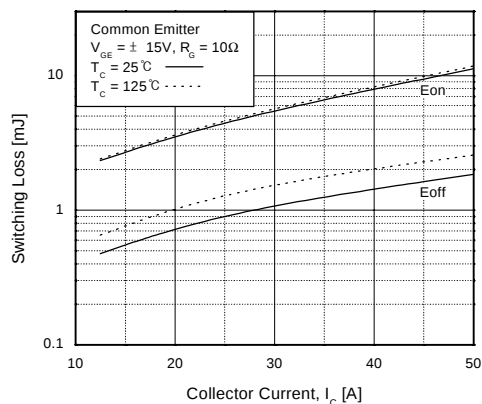
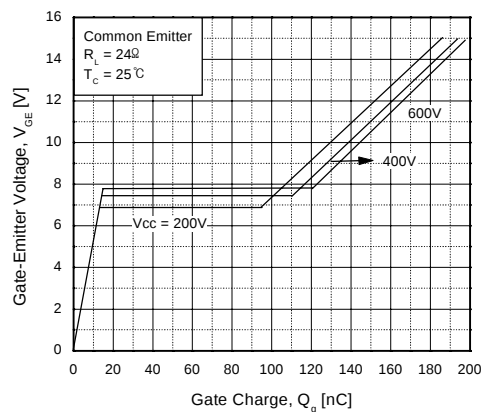
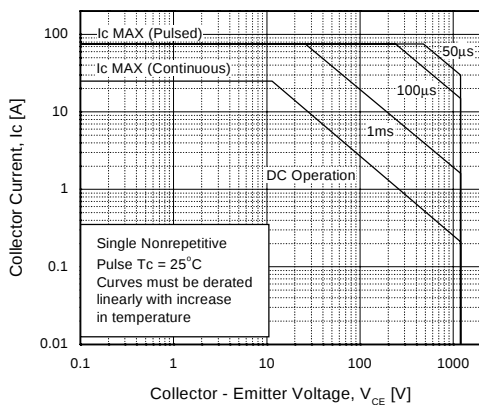
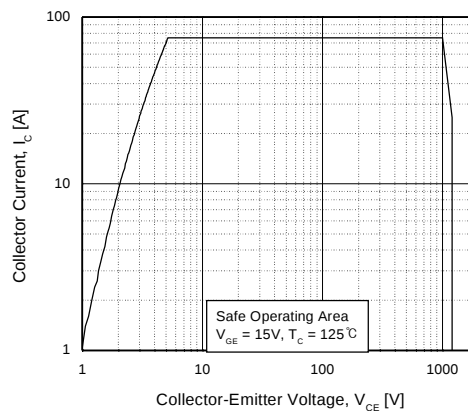
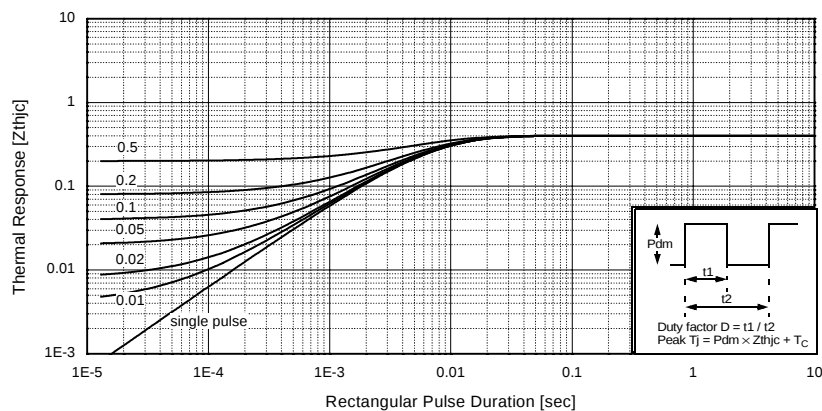
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	--	2100	--	pF
C _{oes}	Output Capacitance		--	180	--	pF
C _{res}	Reverse Transfer Capacitance		--	90	--	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 25A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	--	60	--	ns
t _r	Rise Time		--	60	--	ns
t _{d(off)}	Turn-Off Delay Time		--	170	--	ns
t _f	Fall Time		--	45	90	ns
E _{on}	Turn-On Switching Loss		--	4.8	7.2	mJ
E _{off}	Turn-Off Switching Loss		--	1.0	1.5	mJ
E _{ts}	Total Switching Loss	V _{CC} = 600 V, I _C = 25A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C	--	5.7	8.7	mJ
t _{d(on)}	Turn-On Delay Time		--	60	--	ns
t _r	Rise Time		--	60	--	ns
t _{d(off)}	Turn-Off Delay Time		--	180	--	ns
t _f	Fall Time		--	70	--	ns
E _{on}	Turn-On Switching Loss		--	5.5	--	mJ
E _{off}	Turn-Off Switching Loss	V _{CE} = 600 V, I _C = 25A, V _{GE} = 15V	--	1.4	--	mJ
E _{ts}	Total Switching Loss		--	6.9	--	mJ
Q _g	Total Gate Charge		--	200	300	nC
Q _{ge}	Gate-Emitter Charge	Measured 5mm from PKG	--	15	23	nC
Q _{gc}	Gate-Collector Charge		--	105	160	nC
L _e	Internal Emitter Inductance		--	14	--	nH


Fig 1. Typical Output Characteristics

Fig 2. Typical Saturation Voltage Characteristics

Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

Fig 4. Load Current vs. Frequency

Fig 5. Saturation Voltage vs. V_{GE}

Fig 6. Saturation Voltage vs. V_{GE}


Fig 7. Capacitance Characteristics

Fig 8. Turn-On Characteristics vs. Gate Resistance

Fig 9. Turn-Off Characteristics vs. Gate Resistance

Fig 10. Switching Loss vs. Gate Resistance

Fig 11. Turn-On Characteristics vs. Collector Current

Fig 12. Turn-Off Characteristics vs. Collector Current


Fig 13. Switching Loss vs. Collector Current

Fig 14. Gate Charge Characteristics

Fig 15. SOA Characteristics

Fig 16. Turn-Off SOA

Fig 17. Transient Thermal Impedance of IGBT

Package Dimension

TO-3P (FS PKG CODE)

